



安徽富信半导体科技有限公司

ANHUI FOSAN SEMICONDUCTOR TECHNOLOGY CO., LTD.

SS115-SS120

SMA Schottky Barrier Rectifier Diode 肖特基势垒整流二极管

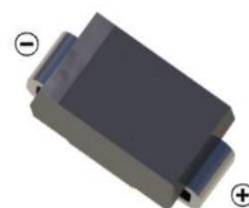
■ Features 特点

Low forward voltage drop 低正向压降

High current capability 高电流能力

Surface mount device 表面贴装器件

Case 封装:SMA(DO-214AC)



■ Maximum Rating 最大额定值

($T_A=25^{\circ}\text{C}$ unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	SS115	SS120	Unit 单位
Peak Reverse Voltage 反向峰值电压	V_{RRM}	150	200	V
DC Reverse Voltage 直流反向电压	V_R	150	200	V
RMS Reverse Voltage 反向电压均方根值	$V_{R(RMS)}$	105	140	V
Forward Rectified Current 正向整流电流	I_F	1		A
Peak Surge Current 峰值浪涌电流	I_{FSM}	30		A
Thermal Resistance J-A 结到环境热阻	$R_{\theta JA}$	50		$^{\circ}\text{C}/\text{W}$
Junction Temperature 结温	T_J	150		$^{\circ}\text{C}$
Storage Temperature 储藏温度	T_{stg}	-65to+150 $^{\circ}\text{C}$		$^{\circ}\text{C}$

■ Electrical Characteristics 电特性

($T_A=25^{\circ}\text{C}$ unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	SS115	SS120	Unit 单位	Condition 条件
Forward Voltage 正向电压	V_F	0.92		V	$I_F=1\text{A}$
Reverse Current 反向电流	$I_R(25^{\circ}\text{C})$ (100°C)	0.05	10	mA	$V_R=V_{RRM}$
Diode Capacitance 二极管电容	C_D	110		pF	$V_R=4\text{V}, f=1\text{MHz}$

■ Typical Characteristic Curve 典型特性曲线

FIG.1-TYPICAL FORWARD CURRENT DERATING CURVE

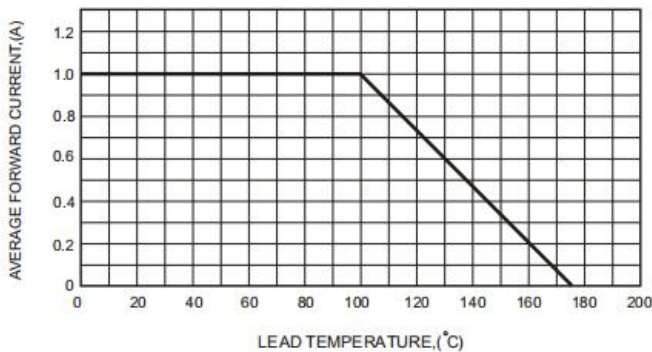


FIG.2-TYPICAL FORWARD CHARACTERISTICS

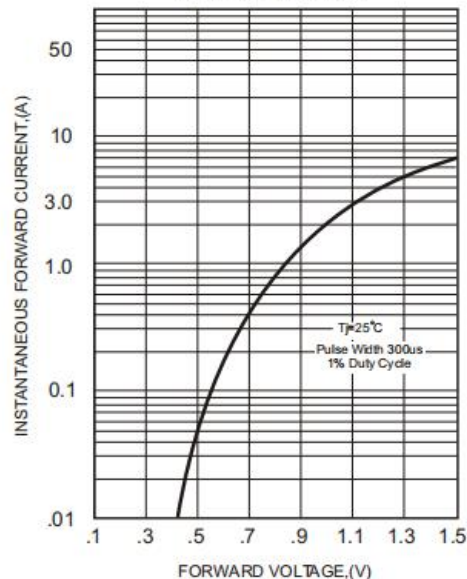


FIG.3-MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

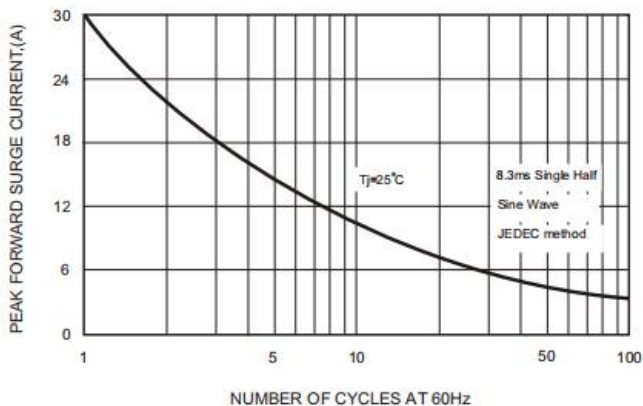


FIG.5 - TYPICAL REVERSE CHARACTERISTICS

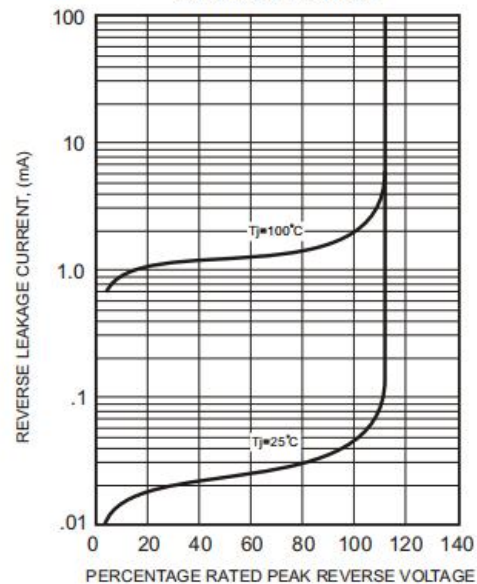
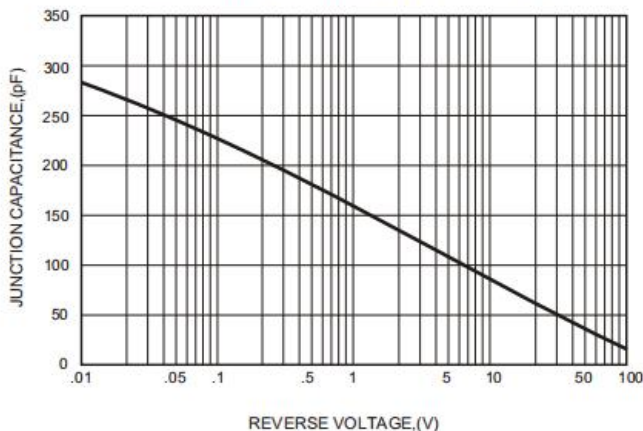
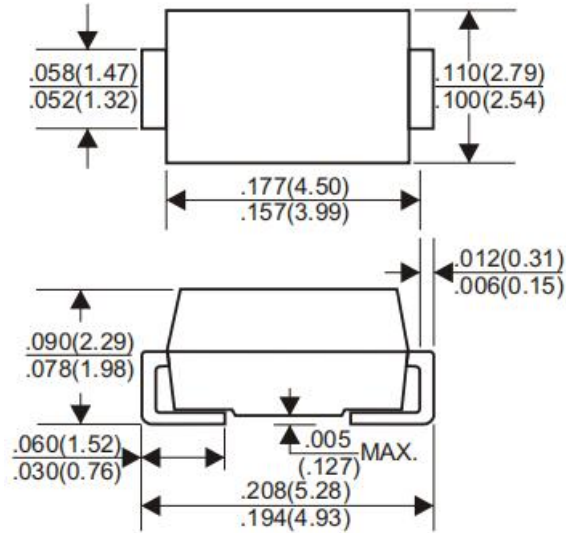


FIG.4-TYPICAL JUNCTION CAPACITANCE



■Dimension 外形封装尺寸

DO-214AC(SMA)



Dimensions in inches and (millimeters)